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### Title

Correction to: Wafer-Scale Fabrication of Sub-10 nm TiO<sub>2</sub>-Ga<sub>2</sub>O<sub>3</sub> n-p Heterojunctions with Efficient Photocatalytic Activity by Atomic Layer Deposition

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### Authors

Xu, Hongyan

Han, Feng

Xia, Chengkai

et al.

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CORRECTION

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# Correction to: Wafer-Scale Fabrication of Sub-10 nm TiO<sub>2</sub>-Ga<sub>2</sub>O<sub>3</sub> n-p Heterojunctions with Efficient Photocatalytic Activity by Atomic Layer Deposition

Hongyan Xu<sup>1</sup>, Feng Han<sup>1</sup>, Chengkai Xia<sup>1</sup>, Siyan Wang<sup>1</sup>, Ranjith K. Ramachandran<sup>2</sup>, Christophe Detavernier<sup>2</sup>, Minsong Wei<sup>3</sup>, Liwei Lin<sup>3</sup> and Serge Zhuiykov<sup>1,4\*</sup>

## Correction to: *Nanoscale Res Lett*

<https://doi.org/10.1186/s11671-019-2991-1>

Please be advised that the name of one of the coauthors in the original article [1] has been incorrectly spelled: '*Ranish M. Ramachandran*' should be '*Ranjith K. Ramachandran*'.

The authors apologize for this error.

### Author details

<sup>1</sup>School of Materials Science and Engineering, North University of China, Taiyuan 030051, People's Republic of China. <sup>2</sup>Department of Solid State Science, Ghent University, Krijgslaan 281/S1, B-9000 Ghent, Belgium. <sup>3</sup>Berkeley Sensor and Actuator Center, Department of Mechanical Engineering, University of California, Berkeley, CA 94720, USA. <sup>4</sup>Ghent University Global Campus, 119 Songdomunhwa-ro, Yeonsu-gu, Incheon 21985, South Korea.

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1. Xu et al (2019) Wafer-Scale Fabrication of Sub-10 nm TiO<sub>2</sub>-Ga<sub>2</sub>O<sub>3</sub> n-p Heterojunctions with Efficient Photocatalytic Activity by Atomic Layer Deposition. *Nanoscale Res Lett* 14:163. <https://doi.org/10.1186/s11671-019-2991-1>

\* Correspondence: [serge.zhuiykov@ugent.be](mailto:serge.zhuiykov@ugent.be)

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<sup>1</sup>School of Materials Science and Engineering, North University of China, Taiyuan 030051, People's Republic of China

<sup>4</sup>Ghent University Global Campus, 119 Songdomunhwa-ro, Yeonsu-gu, Incheon 21985, South Korea

Full list of author information is available at the end of the article